

MBR2070CT - MBR20100CT

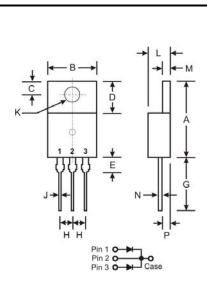
20A HIGH VOLTAGE SCHOTTKY BARRIER RECTIFIER

Features

- Guard Ring Die Construction for **Transient Protection**
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Lead Free Finish/RoHS Compliant (Note 3)

Mechanical Data

- Case: TO-220AB •
- Case Material: Molded Plastic. UL Flammability . Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Polarity: As Marked on Body
- Terminals: Finish Tin. Solderable per MIL-STD-202, Method 208 (e3)
- Marking: Type Number
- Ordering Information: See Page 2
- Weight: 2.24 grams (approximate)



TO-220AB					
Dim	Min Max				
Α	14.48	15.75			
В	10.00	10.40			
С	2.54	3.43			
D	5.90	6.40			
Е	2.80	3.93			
G	12.70	14.27			
Н	2.40	2.70			
J	0.69	0.93			
К	3.54	3.78			
L	4.07	4.82			
м	1.15	1.39			
N	0.30	0.50			
Р	2.04	2.79			
All Dimensions in mm					

Maximum Ratings and Electrical Characteristics $@T_A = 25^{\circ}C$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

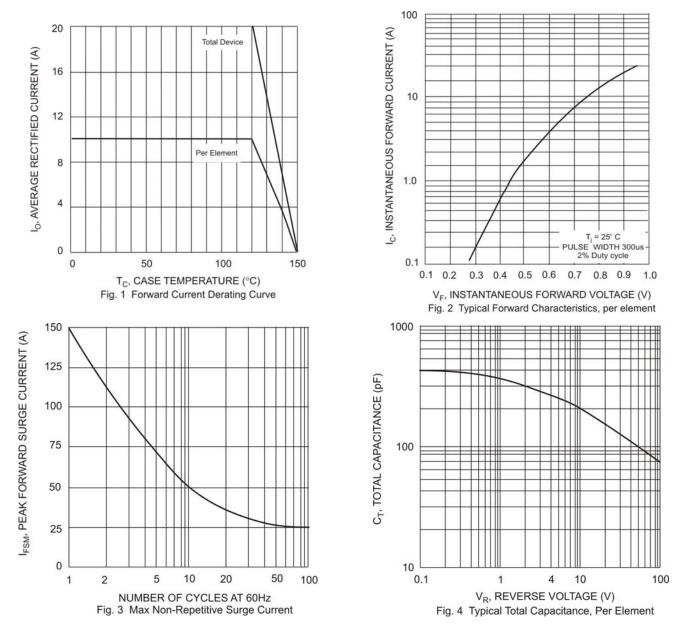
Characteristic		Symbol	MBR 2070CT	MBR 2080CT	MBR 2090CT	MBR 20100CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	70	80	90	100	V
RMS Reverse Voltage		V _{R(RMS)}	49	56	63	70	V
Average Rectified Output Current (Note 1) @ T _c = 120°C		lo	20			А	
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load		I _{FSM}	150			А	
@ @ _F	$F = 10A, T_i = 125^{\circ}C$ $F = 10A, T_i = 25^{\circ}C$ $F = 20A, T_i = 125^{\circ}C$ $F = 20A, T_i = 25^{\circ}C$	V_{FM}	0.75 0.85 0.85 0.95			V	
Peak Reverse Current at Rated DC Blocking Voltage (Note 4)	@ T _A = 25°C @ T _A = 125°C	I _{RM}		-	10 00		mA
Typical Total Capacitance (Note 2)		CT	1000			pF	
Typical Thermal Resistance Junction to Case (Note 1)		$R_{ ext{ heta}JC}$	2.0			°C/W	
Voltage Rate of Change		dV/dt	10000			V/µs	
Operating Temperature Range		Tj	-55 to +150			°C	
Storage Temperature Range		T _{STG}	-55 to +175		°C		

Notes: 1.

- Thermal resistance junction to case mounted on heatsink. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC and per element. 2.
- 3. RoHS revision 13.2.2003. Glass and high temperature solder exemptions applied, see EU Directive Annex Notes 5 and 7.

4. Short duration pulse test to minimize self-heating effect.





Ordering Information (Note 5)

Device	Packaging	Shipping
MBR20xxCT*	TO-220AB	50/Tube

xx = Device type, e.g. MBR2080CT

Notes: 5. For packaging details, visit our website at http://www.diodes.com/datasheets/ap02008.pdf.

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